

# Model building and testing procedure – An analogue multiplexer SPICE macromodel improved with temperature effects

Ivailo M. Pandiev<sup>1</sup>

**Abstract** – A systematic procedure to design a behaviour SPICE macromodels is described in this paper. The proposed modelling procedure can be split into three basic steps: 1) structuring the model; 2) build the model; 3) validate the model. Using this method, an improved SPICE macromodel of a CMOS analogue multiplexer is presented in which the temperature effect of a switch on-resistance is modelled. Also, for creating the simulation model, techniques known from modelling operational amplifiers have been adapted. The proposed macromodel allows the simulation of circuits with respect to the behaviour in both the time and frequency domains, including error parameters and the temperature dependence of switch on-resistance. Model parameters for the integrated circuit ADG408 from Analog Devices are extracted as an example. The simulation results are compared with manufacturer's data and good correspondence is reported.

**Keywords** – Analogue circuits, Temperature effects, CMOS analogue multiplexers, SPICE, Modelling.

## I. INTRODUCTION

The CMOS analogue multiplexers have become an essential component in the design of electronic systems which require the ability to control and select a specified transition path for the analogue signal. These analogue devices are widely used for implementing multi-channel amplifiers, sample-and-hold circuits and PGAs. [1-3].

The switch on-resistance ( $R_{ON}$ ) is an important consideration in applying analogue multiplexers. When one of the switches is closed, DC-performance is affected mainly by on-resistance and leakage current. Also  $R_{ON}$  changes as a function of the temperature and from switch-to-switch. However, temperature variation of the switch on-resistance is not presented in the available behaviour SPICE macromodels of analogue multiplexers [4, 5]. The majority of published SPICE macromodels only attempt to model  $R_{ON}$ , usually by a fixed on-resistance model parameter, defined into the ideal model with voltage-controlled switches. They therefore cannot be used to simulate the dynamic variations in  $R_{ON}$  due to changing temperature. To solve this problem, here is proposed a design procedure for modelling temperature dependence of the on-resistance in the CMOS analogue multiplexer macromodels. Also, techniques described in [6-8] have been adapted for macromodelling the temperature effects.

## II. MACROMODEL BUILDING PROCEDURE

The macromodel building and testing procedure presented in this section is based on a Top-Down analysis approach and by applying simplification and build-up technique, known from modelling operational amplifiers [9-12].

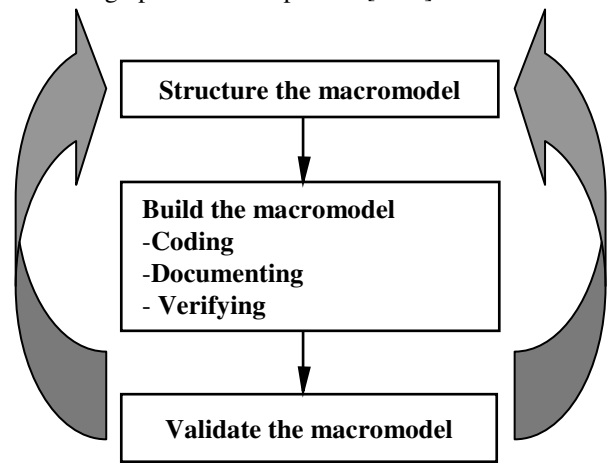


Fig. 1. Model building and testing procedure.

The process of model building and testing, as shown in Fig. 1, can be broken down into three steps: 1) structure the model; 2) build the model; 3) validate the model. Despite the fact that the process of model building is shown in a linear fashion, moving between structuring, building and validation of the model is a process that has iterative nature.

Each step of the procedure can be split into smaller steps which follow a similar iterative pattern. An outline of these steps can be resumed as follows.

1) The first step is to choose an internal structure for the model. The structure can be different from the actual structure of the IC. Also, the structure should consist of the elements that need to be defined and the data and logic, required to drive the model. It effectively is a paper version of the computer model.

2) The second step is the building of the model with the simulation software. This process consists of three distinct activities: coding, entering the model into the computer; documenting, explaining the model structure using software facilities and other techniques; verifying, ensuring that the code is correct. Each of these activities is performed in small steps, iteratively building and improving the model.

3) The last step is the validation of the macromodel. Validation is the process of determining whether a simulation model

<sup>1</sup>Ivailo M. Pandiev is with the Faculty of Electronics from Technical University of Sofia, Kliment Ohridski 8, 1000 Sofia, Bulgaria. E-mail: ipandiev@tu-sofia.bg



where  $R_{ON}(T_0)$  is the switch on-resistance at a temperature  $T_0 = 27^\circ\text{C}$ .

The temperature coefficients  $TC1$  and  $TC2$ , and the resistance  $R_T(T_0)$  from Eq. (2) are calculated by employing the least squares sense technique.

The main advantage of this approach is that parameter extraction can be performed only from manufacturer's data, even for integrated circuits whose internal structure is unknown.

Another temperature stage with an exponential behaviour is shown in Fig. 3. It consists of the voltage source  $V_{TE}$ , the diode  $D_{TE}$  and the correction current source  $I_{TE}$ . The exponential temperature dependence of saturation current  $I_S(T)$  in the SPICE diode model [13] is determined by

$$I_S(T) = I_{So} e^{(T/T_0 - 1)E_G / (NV_T)} (T/T_0)^{XTI/N} \quad (5)$$

where  $I_{So}$  is the saturation current at  $T_o$ ,  $T$  is the temperature in  $K$  (Kelvin),  $XTI$  is the saturation current temperature exponent,  $N$  is the emission coefficient,  $V_T$  is the thermal voltage, and  $E_G$  is the energy gap. The parameter extraction can be done for the desired temperature behaviour. The voltage source  $V_{TE}$  is fixed at  $-10\text{V}$  to provide a reverse voltage drop across  $D_{TE}$ . The resistor  $R_{TE}$  is set to  $1\Omega$  in order to minimize the generated thermal noise and to simplify the calculations for the other components in the stage.

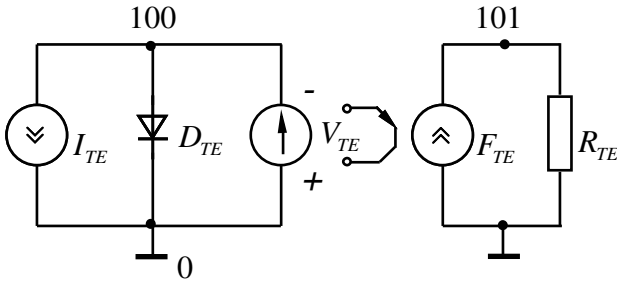


Fig. 3. Stage for generating exponential temperature dependence of the  $R_{ON}$ .

The current  $I_S(T)$ , generated from  $D_{TE}$ , will flow through the voltage source  $V_{TE}$  towards the ground. The current  $I_S(T)$  is an exponential temperature-controlled input value for current-controlled current source (CCCS)  $F_{TE}$ , defined in the macromodel. The current generated by the  $F_{TE}$  will have the following form:

$$I(F_{TE}) = k_{1,TE} I_{VTE}(T) \quad (6)$$

The leakage current thus generated,  $I(F_{TE})$  is routed through the resistor  $R_{TE}$ . The linear coefficient  $k_{1,TE}$  of the CCCS is selected to be equal to one. The voltage  $V_{101}$  works as a linear temperature-controlled input value for VCCS  $G_T$  in the model.

### III. MACROMODEL PERFORMANCE

The performance of the macromodel has been compared with data sheet parameters of the integrated analogue multiplexer ADG408 [14]. The existing macromodel for the ADG408 was used, with additional elements modelling a quadratic temperature function of the switch on-resistance (Fig. 2), inserted between the node 73 and the output terminal.

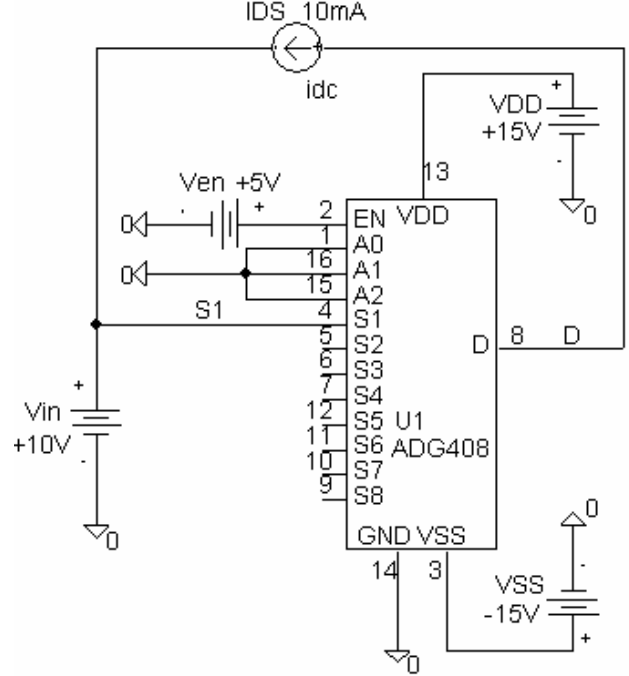


Fig. 4. Test circuit for simulation.

The test circuit for simulation shown in Fig. 4 is created following the test conditions, given in the semiconductor data book of the corresponding IC. The power supply voltages of the circuit are chosen  $\pm 15\text{V}$  and logic supply voltage is set to  $+5\text{V}$ . The DC input signal level  $V_{in}$ , applied to node S1 (pin 4), is set to  $+10\text{V}$ . The ideal current sources  $I_{DS} = 10\text{mA}$  is connected between nodes S1 and D. For the simulation testing a parametric DC analysis is performed with the sweep parameters within the range from  $V_{in} = -15\text{V}$  to  $V_{in} = +15\text{V}$ . The enabling input voltage source  $V_{EN} = +5\text{V}$  is applied to node EN (pin 2). The computer simulations are implemented for three values of the temperature, namely  $25^\circ\text{C}$ ,  $85^\circ\text{C}$  and  $125^\circ\text{C}$ . Figure 5 and 6 shows the on-resistance versus input voltage for different temperature of the real device ADG408 and the simulation output, using the values in the netlist of Table 1. In Table 1 only additional elements to the existing model [4] are represented. Notice that the simulated response compares quite closely with the actual response. The maximum error between simulation results and manufacturer's data are not higher than 10%, which guarantees the sufficient degree of accuracy.

Table 1. SPICE netlist of the output section for ADG408 model.

```

.SUBCKT ADG408/AD-X 4 5 6 7 12 11 10 9 15 16 1 2 8 13 14 3
* Section for control line A0, A1 and A2
* Main Series Switch combination
* Output and enable switch section *** see Reference [4] ***
GT 73 88 POLY(2) (73 88) (100 0) 0 0 0 0 1
S_EN_1 88 8 2 14 Sdemux
C_EN_1 2 8 4.2E-12 ; SETS CHARGE INJECTION
.MODEL Sdemux VSWITCH (RON=1 ROFF=1E12 VON=2.0
VOFF=1.4)
* Temperature stage
IT 0 100 1
RT 0 100 0.95692800467
+ TC -0.02224408931100 1.306292978368239e-004
.ENDS

```

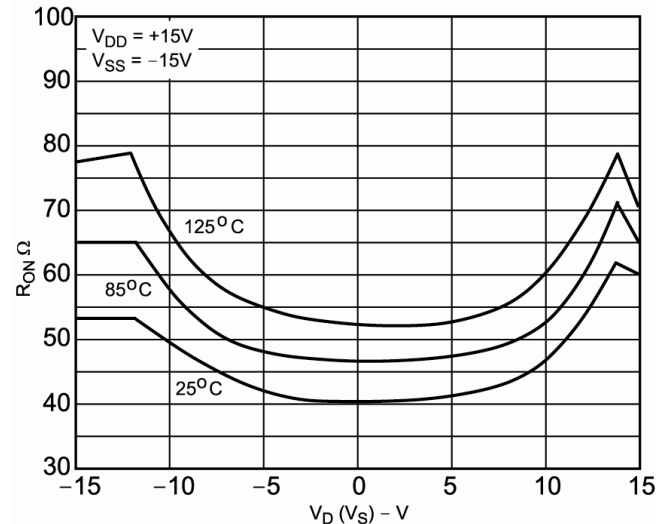


Fig. 5. ADG408 temperature effects.

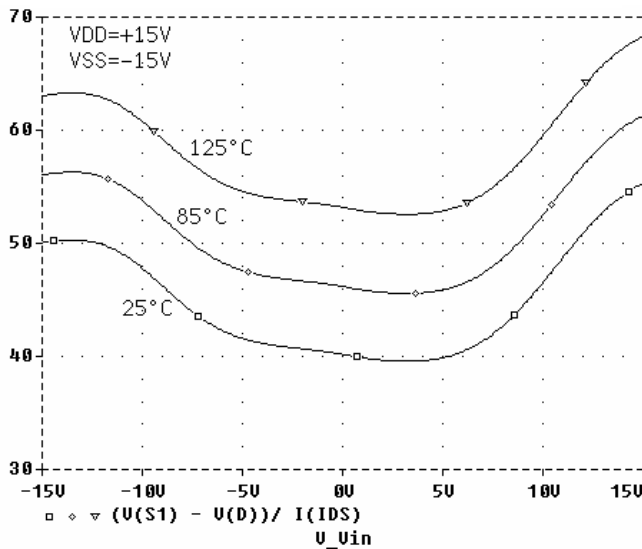


Fig. 6. ADG408 simulated temperature effects.

## IV. CONCLUSIONS

This paper presents the development of the analogue multiplexer SPICE macromodel, aimed at improving the modelling of switch on-resistance as a function of temperature. Modelling of the temperature effects of the circuit is independent from the actual technical realizations and the model parameters and can only be obtained from manufacturer's data of the real IC. The macromodel can be used to simulate different kinds of analogue circuits in respect to temperature variations. The detailed comparison with semiconductor data book demonstrates a good correspondence with selected diagrams of the analogue multiplexer ADG408 from Analog Devices. The maximum error between simulation results and manufacturer's data is not higher than 10%. However, other analogue multiplexers, especially those using different topologies or technologies, may well exhibit different functions of the on-resistance  $R_{ON}$  versus temperature. These matters are the subjects of further research.

## REFERENCES

- [1] W. Kester, "Switches and Multiplexers. Useful Design Techniques and Tips for Switches and Multiplexers", Analog Devices, Norwood, MA, USA, pp. 7.62-7.66, 2005.
- [2] R. L. Geiger, P. E. Allen and N. R. Strader, *VLSI Design Techniques for Analog and Digital Circuits*, pp. 289-302, McGraw-Hill, 1996.
- [3] *Op Amp Applications*, Analog Devices, Norwood, MA, USA, pp. 6.128-6.129 and pp. 3.26-3.27, 2002.
- [4] Switches/Multiplexers - SPICE Models, Analog Devices 2005, <http://www.analog.com/>.
- [5] *Analog Switches and Multiplexers Macromodels*, Maxim Integrated Products 2005, <http://www.maxim-ic.com/tools/spice>.
- [6] H. Chenmin, D. Leach and Sh. Chan, "An improved macromodel for operational amplifiers," *International Journal of Circuit Theory Applications*, vol. 18, pp. 190-203, 1990.
- [7] U. Jörges, G. Jummel and G. Müller, "A macromodel of sample-and-hold circuits," *International Journal of Circuit Theory Applications*, vol. 25, pp. 483-502, 1997.
- [8] "Development of an extensive SPICE macromodel for current-feedback amplifiers," National Semiconductor, Application Note AN 840, 1992.
- [9] Cousineau, M., D. Standarovski, M. Lescure, *Analog circuit modeling method – Sample-and-Hold model development*, MIXDES 2003, Poland, June 2003, pp. 395-398.
- [10] G.R. Boyle et al., "Macromodeling of integrated circuit operational amplifiers," *IEEE J. of Solid-State Circuits*, vol. SC-9, No 6, pp. 359-363, Dec. 1974.
- [11] A.I. Kayssi, "Macromodel construction and verification," *IEEE J. of Circuit&Devices*, pp. 34-39, 1998.
- [12] A.M. Law, "How to conduct a successful simulation study," *Proceeding of the 2003 Winter Simulation Conference*, pp. 66-70, 2003.
- [13] *MicroSim PSpice A/D Reference Manual*, MicroSim, Irvine, California USA, Chapter 2, 1996.
- [14] CMOS analogue multiplexer ADG408 - data sheet, Analog Devices, Norwood, MA, USA, 2003.